

SKiiP 29ANB08V1



MiniSKiiP® 2

3-phase bridge rectifier +
brake chopper

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Features

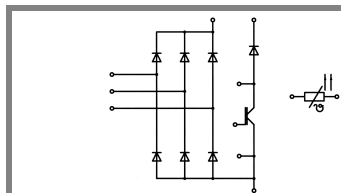
- Ultrafast NPT IGBTs
- Robust and soft freewheeling diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognised file no. E63532

Typical Applications

- Input bridge for Inverter up to 30 kVA

Remarks

- V_{CEsat} , V_F = chip level value



ANB

Absolute Maximum Ratings		T _s = 25 °C, unless otherwise specified	
Symbol	Conditions	Values	Units
IGBT - Chopper			
V _{CES}	T _s = 25 (70) °C t _p ≤ 1 ms	600	V
I _C		125 (93)	A
I _{CRM}		300	A
V _{GES}		± 15	V
T _j		- 40 ... + 150	°C
Diode - Chopper			
I _F	T _s = 25 (70) °C t _p ≤ 1 ms	120 (89)	A
I _{FRM}		300	A
T _j		- 40 ... + 150	°C
Diode - Rectifier			
V _{RRM}	T _s = 70 °C t _p = 10 ms, sin 180 °, T _j = 25 °C t _p = 10 ms, sin 180 °, T _j = 25 °C	800	V
I _F		83	A
I _{FSM}		1000	A
i ² t		6600	A ² s
T _j		- 40 ... + 150	°C
I _{tRMS}		per power terminal (20 A / spring)	120
T _{stg}	T _{op} ≤ T _{stg}	- 40 ... + 125	°C
V _{isol}	AC, 1 min.	2500	V

Characteristics		$T_s = 25\text{ °C}$, unless otherwise specified			
Symbol	Conditions	min.	typ.	max.	Units
IGBT - Chopper					
V_{CEsat}	$I_{Cnom} = 150\text{ A, } T_j = 25\text{ (125) °C}$		2 (2,2)	2,5 (2,7)	V
$V_{GE(th)}$	$V_{GE} = V_{CE}, I_C = 1,5\text{ mA}$	3	4	5	V
$V_{CE(TO)}$	$T_j = 25\text{ (125) °C}$		1,2 (1,1)	1,3 (1,2)	V
r_T	$T_j = 25\text{ (125) °C}$		5,3 (7,3)	8 (10)	mΩ
C_{ies}	$V_{CE} = 25\text{ V, } V_{GE} = 0\text{ V, } f = 1\text{ MHz}$		9		nF
C_{oes}	$V_{CE} = 25\text{ V, } V_{GE} = 0\text{ V, } f = 1\text{ MHz}$		1,7		nF
C_{res}	$V_{CE} = 25\text{ V, } V_{GE} = 0\text{ V, } f = 1\text{ MHz}$		2,1		nF
$R_{th(j-s)}$	per IGBT		0,4		K/W
$t_{d(on)}$	under following conditions		20		ns
t_r	$V_{CC} = 300\text{ V, } V_{GE} = \pm 15\text{ V}$		25		ns
$t_{d(off)}$	$I_{Cnom} = 150\text{ A, } T_j = 125\text{ °C}$		185		ns
t_f	$R_{Gon} = R_{Goff} = 4\text{ Ω}$		15		ns
E_{on}	inductive load		5,7		mJ
E_{off}			3,7		mJ
Diode - Chopper					
$V_F = V_{EC}$	$I_{Fnom} = 150\text{ A, } T_j = 25\text{ (125) °C}$		1,7 (1,7)	2,1 (2,1)	V
$V_{(TO)}$	$T_j = 25\text{ (125) °C}$		1 (0,9)	1,1 (1)	V
r_T	$T_j = 25\text{ (125) °C}$		4,7 (5,3)	6,7 (7,3)	mΩ
$R_{th(j-s)}$	per diode		0,55		K/W
I_{RRM}	under following conditions		270		A
Q_{rr}	$I_{Fnom} = 150\text{ A, } V_R = 300\text{ V}$		18		μC
E_{rr}	$V_{GE} = 0\text{ V, } T_j = 125\text{ °C}$ $di_F/dt = 13700\text{ A/μs}$		3,5		mJ
Diode - Rectifier					
V_F	$I_{Fnom} = 75\text{ A, } T_j = 25\text{ °C}$		1,2		V
$V_{(TO)}$	$T_j = 150\text{ °C}$		0,8		V
r_T	$T_j = 150\text{ °C}$		7		mΩ
$R_{th(j-s)}$	per diode		0,7		K/W
Temperature Sensor					
R_{ts}	3 %, $T_r = 25\text{ (100) °C}$		1000(1670)		Ω
Mechanical Data					
w			65		g
M_s	Mounting torque	2		2,5	Nm

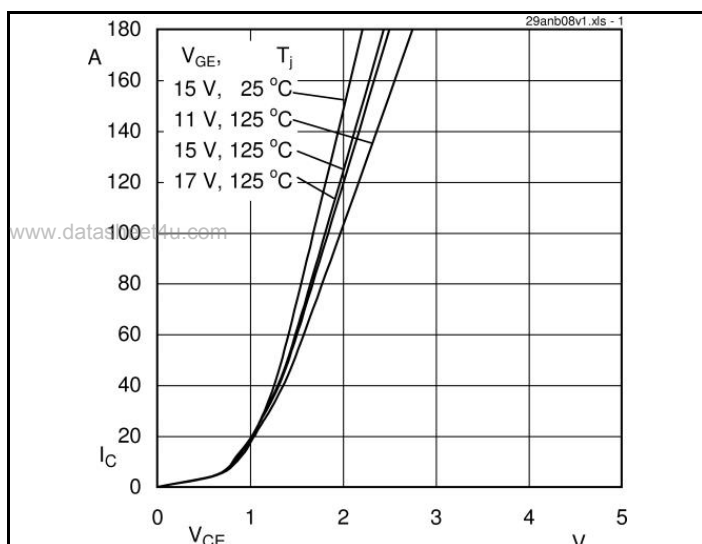


Fig. 1 Typ. output characteristic

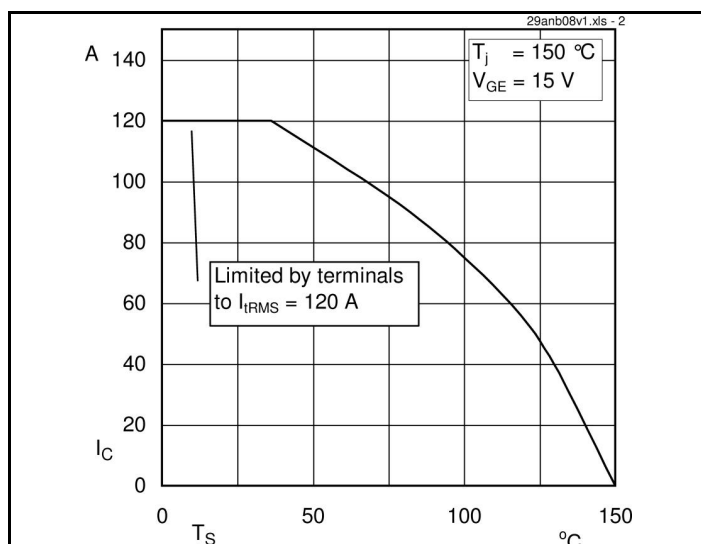


Fig. 2 Typ. rated current vs. temperature

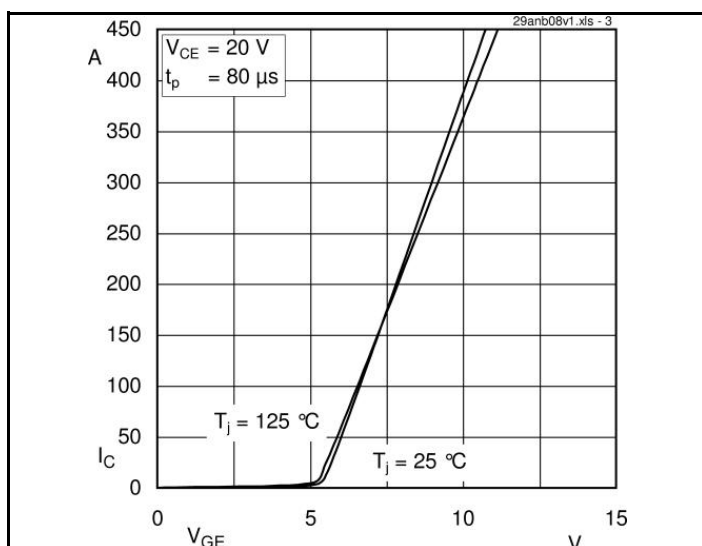


Fig. 3 Typ. transfer characteristic

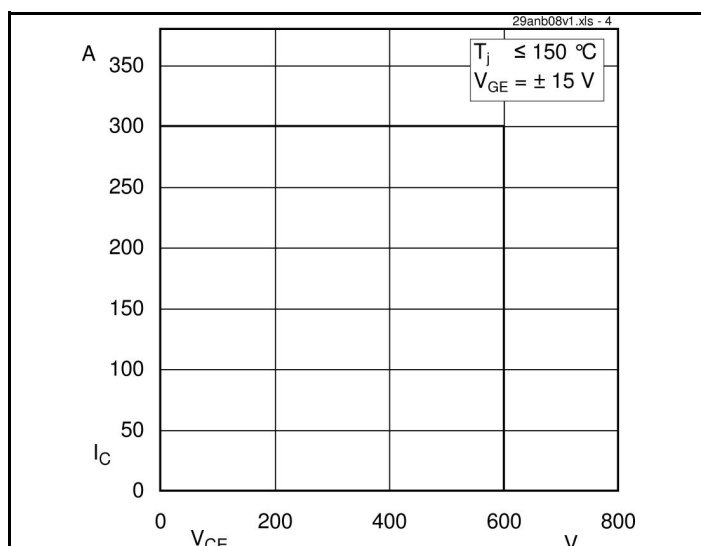


Fig. 4 Reverse bias safe operating area

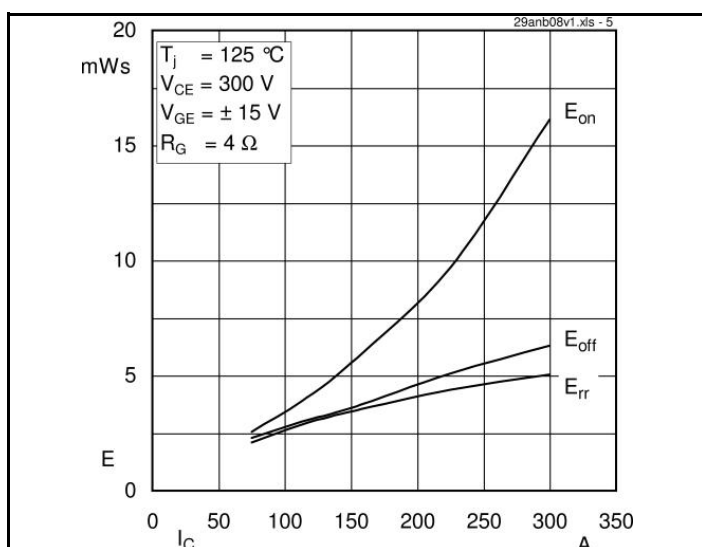


Fig. 5 Typ. Turn-on /-off energy = $f(I_C)$

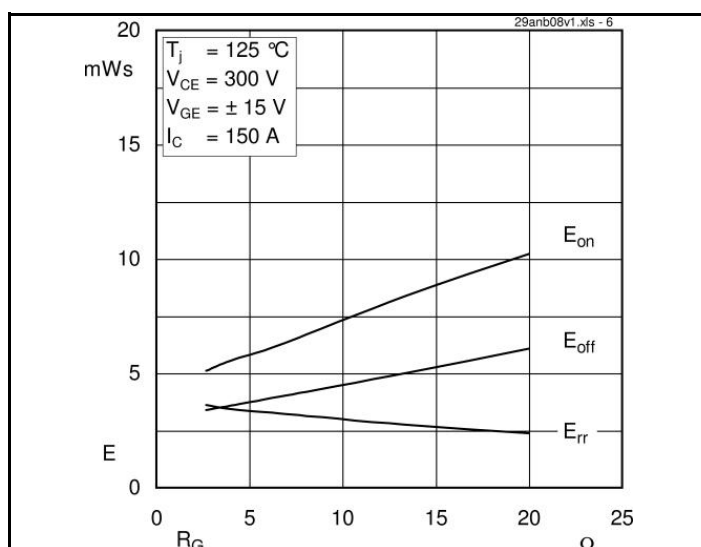
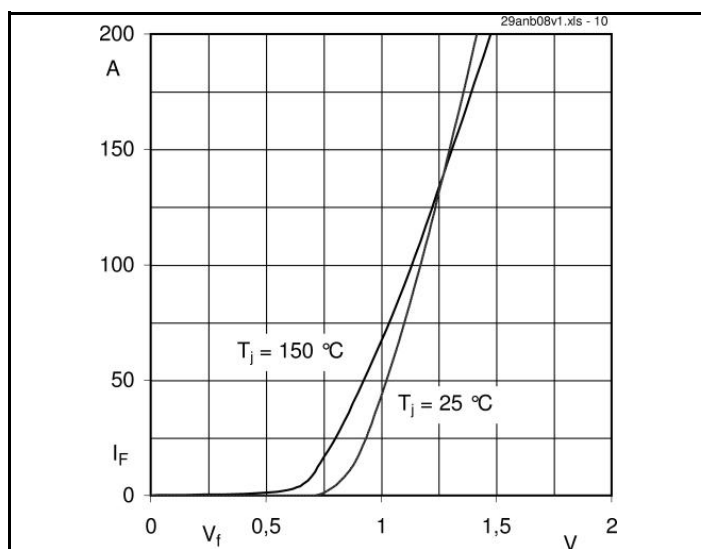
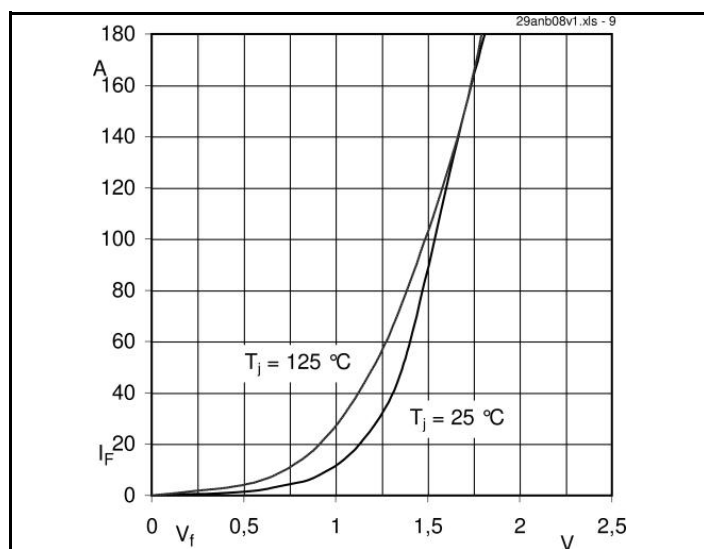
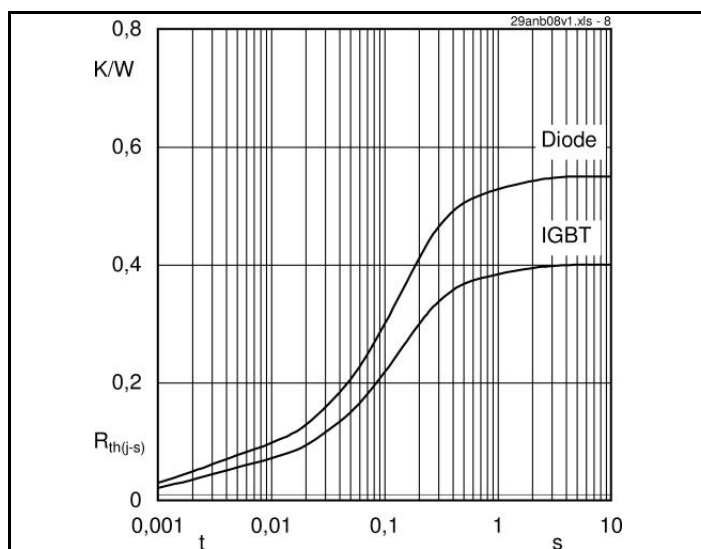
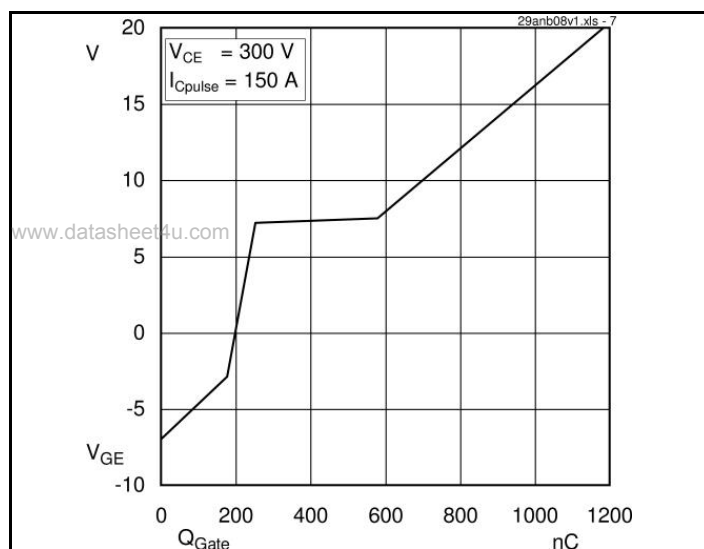
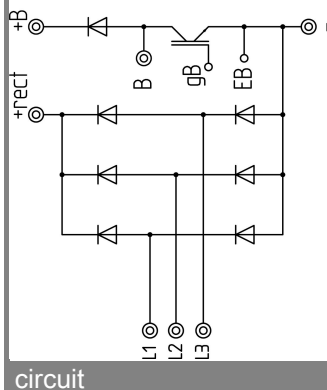


Fig. 6 Typ. Turn-on /-off energy = $f(R_G)$





pinout, dimensions

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